

Amendments to the Claims:

Please amend claim 69 as follows:

1-68. (Cancelled)

69. (Currently amended) A microelectronic die, comprising:

a substrate having a first portion with a first surface, a second portion with a second surface opposite the first surface, and a separation plane between the unseparated first and second portions, the first portion projecting from the second portion and having first and second voids extending from the first surface to the separation plane, the first void tapered along a first axis and the second void tapered along a second axis generally parallel to the first axis, the first and second tapered voids being larger toward the separation plane; and

at least one operable microelectronic device disposed at least proximate to the first surface and between the first and second axes.

70. (Previously Presented) The microelectronic die of claim 69 wherein the at least one operable microelectronic device is disposed in the first portion of the substrate between the first and second tapered voids.

71. (Previously Presented) The microelectronic die of claim 69 wherein the first portion and the second portion have at least generally the same composition.

72. (Previously Presented) The microelectronic die of claim 69 wherein the first surface is separated from the separation plane by approximately 150 microns or less.

73. (Previously Presented) The microelectronic die of claim 69 wherein the first and second voids are etched voids.

74. (Previously Presented) The microelectronic die of claim 69 wherein the first portion further includes a third void extending from the first surface to the separation plane, and wherein the first, second, and third voids are regularly spaced apart from each other.

75. (Previously Presented) The microelectronic die of claim 69 wherein the first portion further includes a third void extending from the first surface to the separation plane, and wherein the first, second, and third voids are randomly spaced apart from each other.

76. (Previously Presented) The microelectronic die of claim 69 wherein the first and second voids each include a first end proximate to the first surface, and wherein the first ends are filled with a filler material.

77. (Previously Presented) The microelectronic die of claim 69 wherein the first and second portions of the substrate comprise silicon.

78. (Previously Presented) The microelectronic die of claim 69, further comprising a film layer disposed on the first surface.

79. (Previously Presented) The microelectronic die of claim 78 wherein the film layer has an external surface facing an opposite direction from the second surface of the second portion, and wherein a distance between the external surface and the separation plane is less than approximately 150 microns.

80. (Previously Presented) The microelectronic die of claim 69 wherein the first and second voids have a conical configuration.

81. (Previously Presented) The microelectronic die of claim 69 wherein the first void has a first depth and the second void has a second depth at least approximately equal to the first depth.